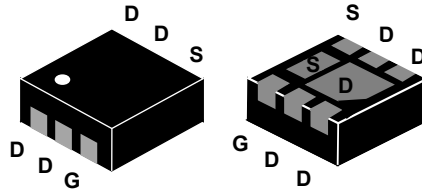
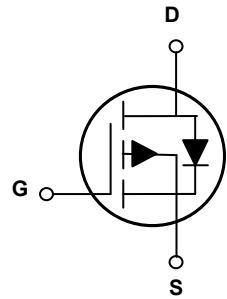


## Main Product Characteristics

$BV_{DSS}$	-20V
$R_{DS(ON)}$	21m $\Omega$ (Max.)
$I_D$	-10A



DFN2x2-6L



Schematic Diagram

## Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



## Description

The GSFB2121A utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

## Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current-Continuous ( $T_C=25^\circ\text{C}$ )	$I_D$	-10	A
Drain Current-Continuous ( $T_C=100^\circ\text{C}$ )		-7	
Drain Current-Pulsed <sup>1</sup>	$I_{DM}$	-40	A
Single Pulse Avalanche Energy <sup>2</sup>	$E_{AS}$	20	mJ
Single Pulse Avalanche Current <sup>2</sup>	$I_{AS}$	-8.8	A
Power Dissipation ( $T_C=25^\circ\text{C}$ )	$P_D$	1.9	W
Power Dissipation-Derate above 25 $^\circ\text{C}$		0.015	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	66	$^\circ\text{C}/\text{W}$
Operating Junction Temperature Range	$T_J$	-55 To +150	$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	-55 To +150	$^\circ\text{C}$

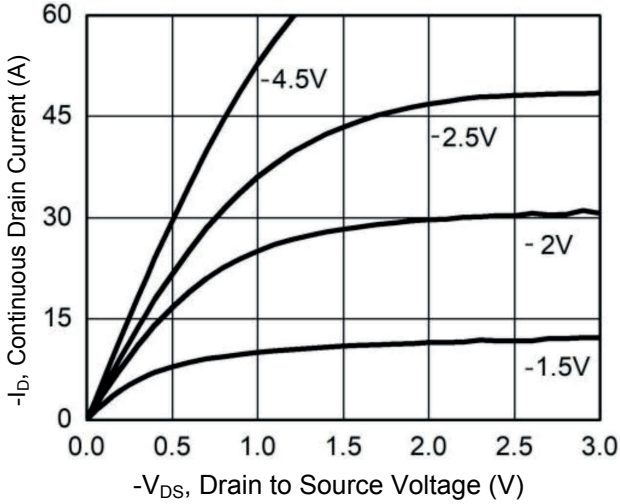
**Electrical Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>On / Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20	-	-	V
$BV_{DSS}$ Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to $25^\circ\text{C}$ , $I_D=-1mA$	-	-0.01	-	$V/^\circ\text{C}$
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS}=-20V, V_{GS}=0V,$ $T_J=25^\circ\text{C}$	-	-	-1	$\mu A$
		$V_{DS}=-16V, V_{GS}=0V,$ $T_J=125^\circ\text{C}$	-	-	-10	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	$\pm 100$	$\mu A$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-5A$	-	16	21	$m\Omega$
		$V_{GS}=-2.5V, I_D=-4A$	-	21	29	$m\Omega$
		$V_{GS}=-1.8V, I_D=-3A$	-	30	41	$m\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS}=-10V, I_S=-5A$	-	15	-	S
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-0.5	-0.7	-1	V
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}$		-	3	-	$mV/^\circ\text{C}$
<b>Dynamic and Switching Characteristics</b>						
Total Gate Charge <sup>2,3</sup>	$Q_g$	$V_{DS}=-10V, I_D=-5A$ $V_{GS}=-4.5V$	-	15	-	nC
Gate-Source Charge <sup>2,3</sup>	$Q_{gs}$		-	2.6	-	
Gate-to-Drain Charge <sup>2,3</sup>	$Q_{gd}$		-	4.3	-	
Turn-On Delay Time <sup>2,3</sup>	$t_{d(on)}$	$V_{DD}=-10V, R_G=3\Omega$ $V_{GS}=-4.5V, I_D=-5A$	-	9	-	nS
Rise Time <sup>2,3</sup>	$t_r$		-	28	-	
Turn-Off Delay Time <sup>2,3</sup>	$t_{d(off)}$		-	24	-	
Fall Time <sup>2,3</sup>	$t_f$		-	7	-	
Input Capacitance	$C_{iss}$	$V_{DS}=-15V, V_{GS}=0V,$ $F=1MHz$	-	1980	-	pF
Output Capacitance	$C_{oss}$		-	242	-	
Reverse Transfer Capacitance	$C_{rss}$		-	126	-	
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Continuous Source Current	$I_S$	$V_G=V_D=0V,$ Force Current	-	-	-10	A
Pulsed Source Current	$I_{SM}$		-	-	-40	A
Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=-1A$ $T_J=25^\circ\text{C}$	-	-	-1	V

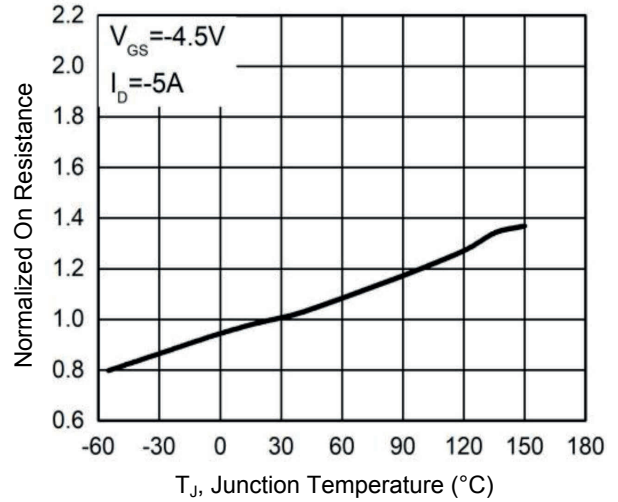
Notes:

1. Repetitive rating: Pulsed width limited by maximum junction temperature.
2.  $V_{DD}=-20V, V_{GS}=-10V, L=0.5mH, R_G=25\Omega$ , starting  $T_J=25^\circ\text{C}$ .
3. Pulse test: pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .

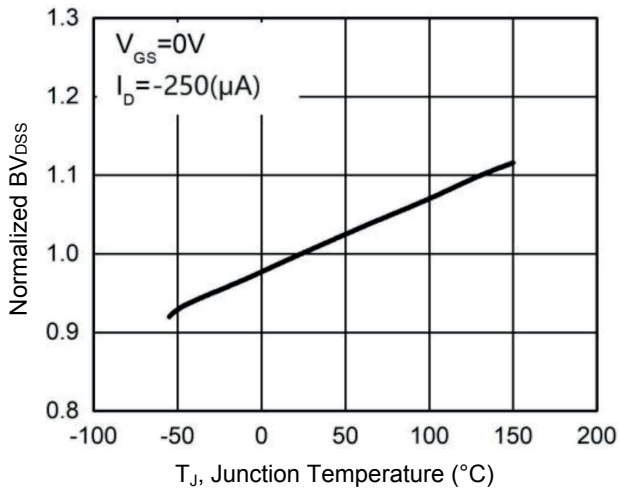
**Typical Electrical and Thermal Characteristic Curves**



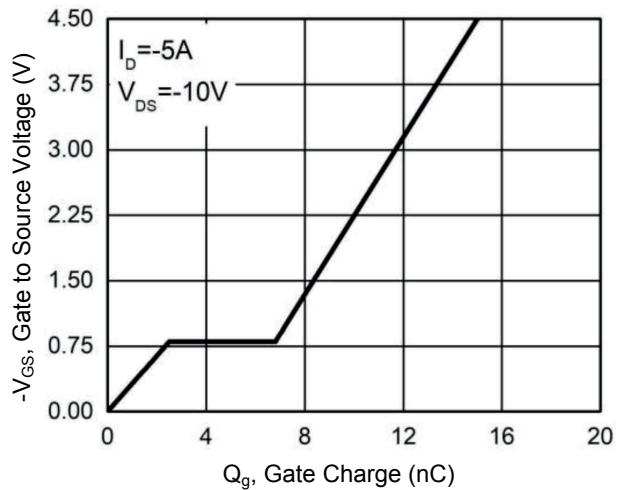
**Figure 1. Output Characteristics**



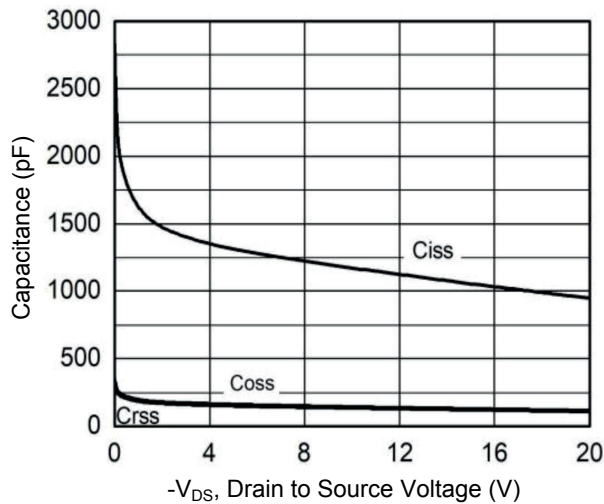
**Figure 2. Normalized  $R_{DS(on)}$  vs.  $T_J$**



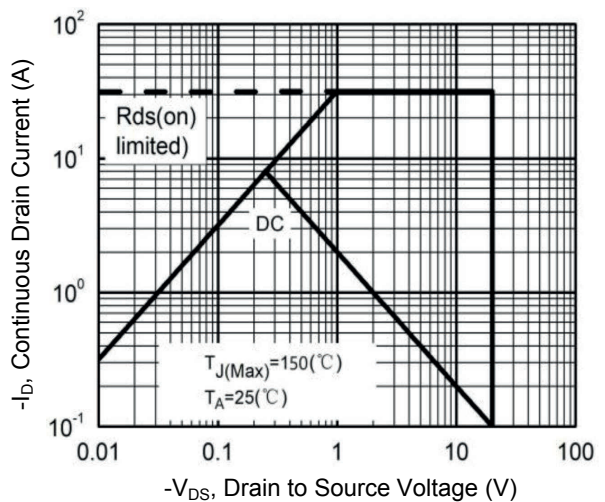
**Figure 3. Normalized  $BV_{DS}$  vs.  $T_J$**



**Figure 4. Gate Charge Waveform**

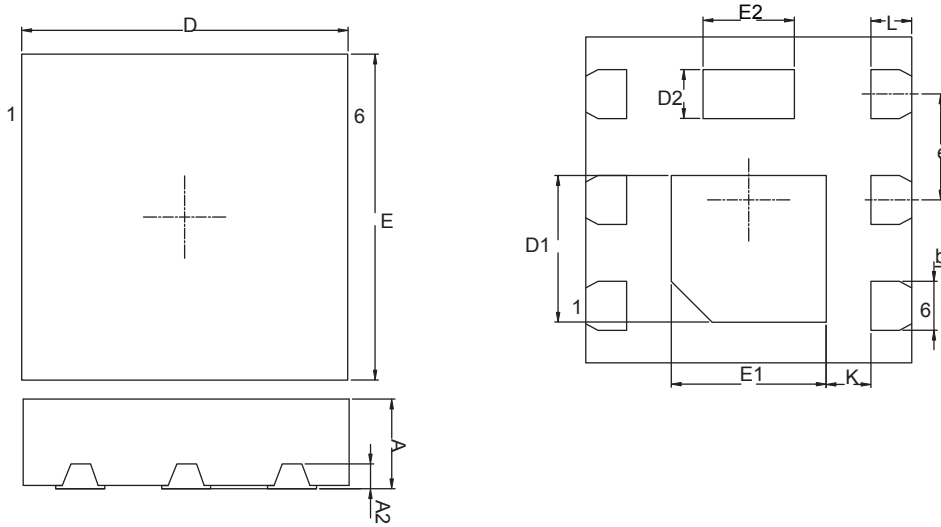


**Figure 5. Capacitance Characteristics**



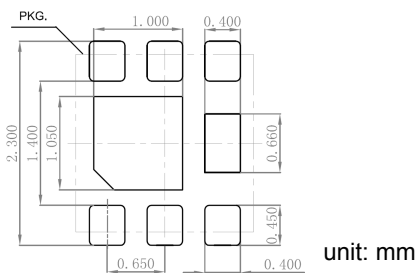
**Figure 6. Maximum Safe Operation Area**

**Package Outline Dimensions (DFN2x2-6L)**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.70	0.80	0.028	0.031
A2	0.152 REF		0.006 REF	
b	0.25	0.35	0.010	0.014
D	1.95	2.05	0.077	0.081
D1	0.80	1.05	0.031	0.041
D2	0.25	0.35	0.010	0.014
E	1.95	2.05	0.077	0.081
E1	0.80	1.00	0.031	0.039
E2	0.46	0.66	0.018	0.026
e	0.650 BSC		0.026 BSC	
L	0.25	0.35	0.010	0.014
K	0.200 MIN		0.008 MIN	

**Recommended Pad Layout**



**Order Information**

Device	Package	Marking	Packaging	SPQ
GSFB2121A	DFN2x2-6L	B2121	Tape & Reel	3,000pcs / Reel